



#9/Amndt B
ATTORNEY DOCKET NO. 43890-449
PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hidenori KAMEI, et al.

Serial No.: 09/680,943

Filed: October 10, 2000

For: P-TYPE NITRIDE SEMICONDUCTOR AND)
METHOD OF MANUFACTURING THE SAME)

) Group Art Unit: 2823

) Examiner: DEVEN M. COLLINS

AMENDMENT UNDER 37 C.F.R. § 1.111

Hon. Assistant Commissioner for Patents
Washington, DC 20231

Sir:

In response to the Office Action dated January 16, 2002, having a shortened statutory period for response set to expire April 16, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 5, without prejudice.

Please amend claim 1 and add new claims 13 and 14 as follows:

1. (Amended) A method for manufacturing p-type nitride semiconductor comprising:

B' a semiconductor layer forming process for forming a (low resistivity) p-type nitride

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